Silicon NPN Power Transistors 2SC2168

DESCRIPTION

·With TO-220 package

·High collector-emitter breakdown voltage

: V_{CEO}=200V(min)

APPLICATIONS

·Power amplifier applications

·TV vertical deflection applications

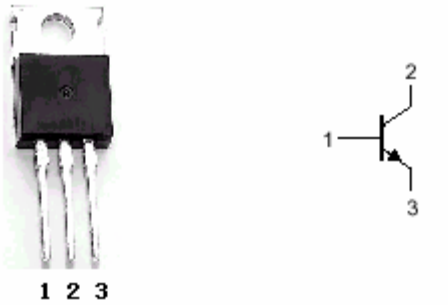


Fig.1 simplified outline (TO-220C) and symbol

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings (Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	200	V
V_{CEO}	Collector-emitter voltage	Open base	200	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		2	A
I_{CM}	Collector current-peak		3	A
P_C	Collector power dissipation	T_C=25□	30	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=25mA ;I_B=0	200			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=0.5mA ;I_E=0	200			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=0.5mA ;I_C=0	6			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=0.5A ;I_B=50m A			1.0	V
I_{CBO}	Collector cut-off current	V_{CB}=200V;I_E=0			10	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			10	μA
h_{FE}	DC current gain	I_C=0.1A ; V_{CE}=5V	50			
f_T	Transition frequency	I_C=0.1A ; V_{CE}=10V		20		MHz

PACKAGE OUTLINE

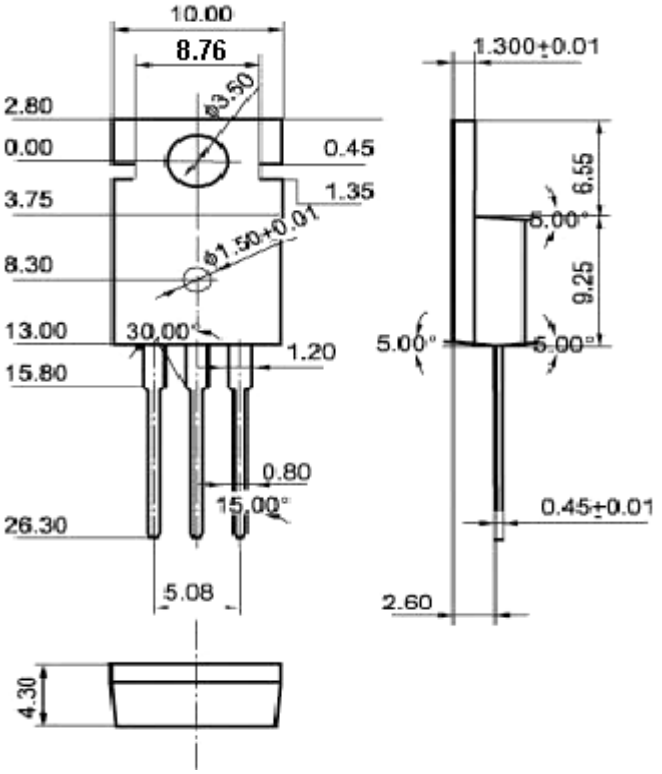


Fig.2 outline dimensions (unindicated tolerance:±0.10 mm)